

Product data sheet

# 1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

### 2. Features and benefits

- Fast switching
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Reduces switching losses in associated MOSFET or IGBT
- Planar passivated for voltage ruggedness and reliability

### 3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply
- Motor drive and SMPS freewheeling diode

## 4. Quick reference data

Table 1. Qu	ick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	1200	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 98 °C; square-wave pulse; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	-	16	A
Static charac	teristics			·		
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 16 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.8	2.7	V
Dynamic cha	acteristics	1			1	
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	ns





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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	к	cathode		К-Ң-А
2	А	anode	-0 <sup>0</sup> 0-	001aaa020
mb	mb	mounting base; connected to cathode	TO-247 (SOD142)	

# 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BYR16W-1200	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
BYR16W-1200	BYR16W-1200

# 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	1200	V
V <sub>RWM</sub>	crest working reverse voltage		-	1200	V
V <sub>R</sub>	reverse voltage	DC	-	1200	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	16	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 98 °C; square-wave pulse	-	32	A

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#### Ultrafast power diode

Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	165	A
T <sub>stg</sub>	storage temperature		-55	150	°C
Tj	junction temperature		-	150	°C

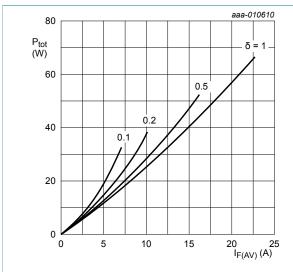
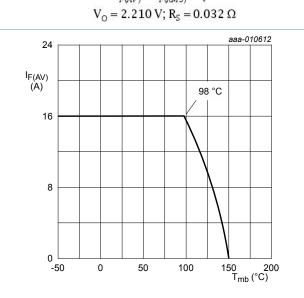


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ 





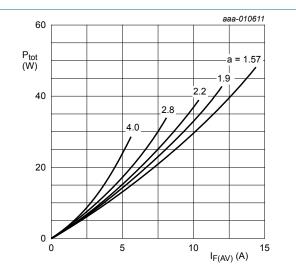
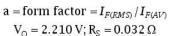
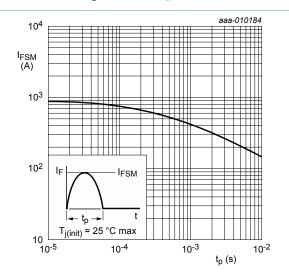


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





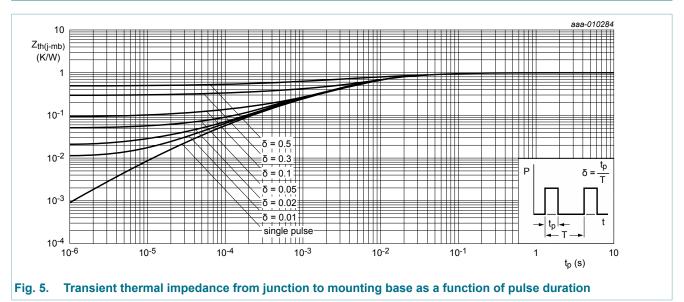
. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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# 9. Thermal characteristics

Table 6.       Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5		-	-	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	45	-	K/W



# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · · · · · · · · · · · · · · ·	1			
V <sub>F</sub> forward voltage	forward voltage	orward voltage $I_F = 16 \text{ A}; T_j = 25 \text{ °C}; Fig. 6$	-	2.3	3	V
	I <sub>F</sub> = 32 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.8	3.9	V	
		I <sub>F</sub> = 16 A; T <sub>j</sub> = 125 °C; <u>Fig. 6</u>	-	1.8	2.7	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 1200 V; T <sub>j</sub> = 25 °C	-	3	100	μA
		V <sub>R</sub> = 1200 V; T <sub>j</sub> = 125 °C	-	0.2	2	mA
Dynamic ch	naracteristics		I			
Q <sub>r</sub> recovered charge	$I_F$ = 16 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 25 °C; <u>Fig. 7</u>	-	520	-	nC	
		$I_F$ = 16 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	1200	-	nC
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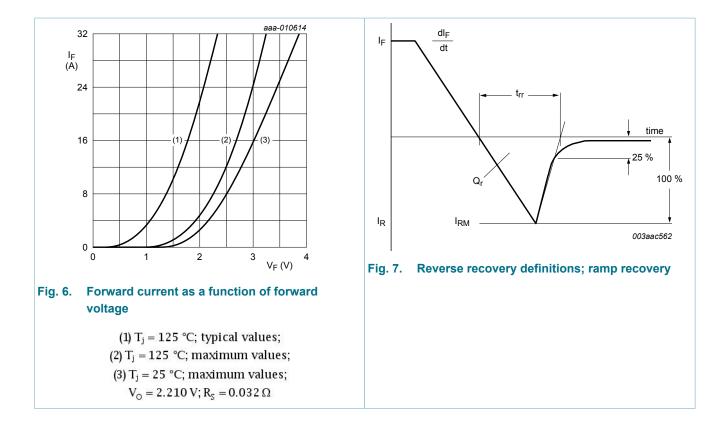
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 \text{ °C}; Fig. 7$	-	605	-	nC
		$I_F$ = 16 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	1600	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	40	-	ns
		$I_F$ = 16 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 25 °C; Fig. 7	-	90	-	ns
		$I_F$ = 16 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	150	-	ns
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 \text{ °C}; Fig. 7$	-	105	-	ns
		$I_F$ = 16 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	200	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	ns
RM	peak reverse recovery current	$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	11.2	-	A
		$I_F$ = 16 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	16	-	A
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu$ s; $T_j = 25 \text{ °C}; Fig. 7$	-	11.2	-	A
		$I_F$ = 16 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 125 °C; <u>Fig. 7</u>	-	16.2	-	A

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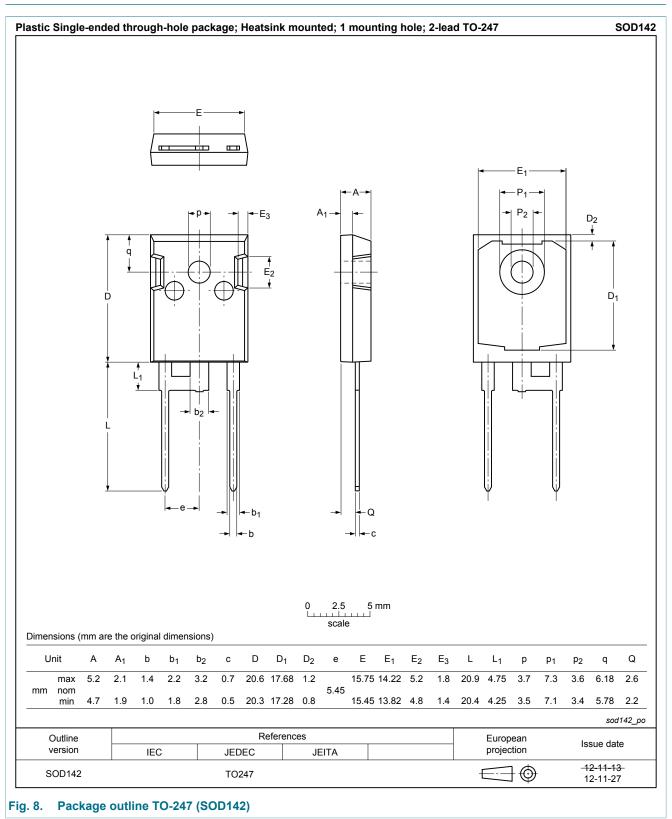
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#### Ultrafast power diode



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## 11. Package outline



BYR16W-1200

Product data sheet

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### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### Ultrafast power diode

### **13. Contents**

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	4
11	Package outline	7
12	Legal information	8
12.1	Data sheet status	8
12.2	Definitions	8
12.3	Disclaimers	8
12.4	Trademarks	9

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